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Hydroxynaphthyridine-Derived Group III Metal Chelates: Wide Band Gap and Deep Blue Analogues of Green Alq₃ (Tris(8-hydroxyquinolate)aluminum) and Their Versatile Applications for Organic Light-Emitting Diodes

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Abstract: A series of group III metal chelates have been synthesized and characterized for the versatile application of organic light-emitting diodes (OLEDs). These metal chelates are based on 4-hydroxy-1,5naphthyridine derivates as chelating ligands, and they are the blue version analogues of well-known green fluorophore Alq₃ (tris(8-hydroxyquinolinato)aluminum). These chelating ligands and their metal chelates were easily prepared with an improved synthetic method, and they were facially purified by a sublimation process, which enables the materials to be readily available in bulk guantity and facilitates their usage in OLEDs. Unlike most currently known blue analogues of Alg₃ or other deep blue materials, metal chelates of 4-hydroxy-1,5-naphthyridine exhibit very deep blue fluorescence, wide band gap energy, high charge carrier mobility, and superior thermal stability. Using a vacuum-thermal-deposition process in the fabrication of OLEDs, we have successfully demonstrated that the application of these unusal hydroxynaphthyridine metal chelates can be very versatile and effective. First, we have solved or alleviated the problem of exciplex formation that took place between the hole-transporting layer and hydroxynaphthyridine metal chelates, of which OLED application has been prohibited to date. Second, these deep blue materials can play various roles in OLED application. They can be a highly efficient nondopant deep blue emitter: maximum external quantum efficiency η_{ext} of 4.2%; Commission Internationale de L'Eclairage x, y coordinates, CIE_{x,y} = 0.15, 0.07. Compared with Alq₃, Bebq₂ (beryllium bis(benzoquinolin-10-olate)), or TPBI (2,2',2"-(1,3,5-phenylene)tris(1-phenyl-1H-benzimidazole), they are a good electron-transporting material: low HOMO energy level of 6.4-6.5 eV and not so high LUMO energy level of 3.0-3.3 eV. They can be ambipolar and possess a high electron mobility of 10^{-4} cm²/V s at an electric field of 6.4×10^5 V/cm. They are a qualified wide band gap host material for efficient blue perylene (CIE_{x,y} = 0.14, 0.17 and maximum η_{ext} 3.8%) or deep blue 9,10-diphenylanthracene (CIE_{x,y} = 0.15, 0.06 and maximum η_{ext} 2.8%). For solid state lighting application, they are desirable as a host material for yellow dopant (rubrene) in achieving high efficiency (η_{ext} 4.3% and $\eta_{\rm P}$ 8.7 lm/W at an electroluminance of 100 cd/m² or $\eta_{\rm ext}$ 3.9% and $\eta_{\rm P}$ 5.1 lm/W at an electroluminance of 1000 cd/m²) white electroluminescence ($CIE_{x,v} = 0.30, 0.35$).

1. Introduction

Efficient electroluminescence (EL) was first reported by Tang and Van Slyke using green light-emitting tris(8-hydroxyquinolinato)aluminum (Alq_3).¹ Very few materials attract attention as much as Alq_3 does in organic light-emitting diodes (OLEDs).² Alq_3 has been used as a green emitter, a common electrontransporting material, and a host material for saturated green and red fluorescent dopants.³ Moreover, due to the rigid balllike geometry, high glass transition temperature ($T_g \sim 175 \text{ °C}$),^{3c} and polymorphic nature,⁴ Alq₃ is readily sublimed to form amorphous thin films, which is beneficial to the fabrication and operation lifetime of OLEDs. To tune its fluorescence color to

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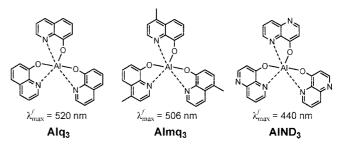
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Downloaded by NATIONAL TAIWAN UNIV on September 10, 2009 | http://pubs.acs.org Publication Date (Web): December 18, 2008 | doi: 10.1021/ja807284e the red or blue region, some structurally modified Alq_3 derivatives have been developed in past two decades to match the requirement in the RGB full color display or white light illumination application. However, most structurally modified Alq_3 derivatives become less thermally stable and less volatile under reduced pressure. Very often, they fail in the fabrication of OLEDs by a thermal-vacuum-deposition process.

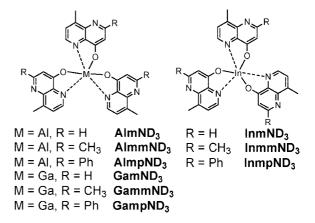
Photophysical and theoretical studies have already provided insight into the electron distribution of the HOMO/LUMO orbitals of Alq₃.^{2,5} Whereas the highest electron density of LUMO is found on pyridine ring, the electrons of HOMO orbitals are located mostly on the phenoxide side of the ligand. An electron-withdrawing substituent on the para-position of the phenoxide ring will deplete the HOMO electron density lowering energy level of the filled states. Following the same rationale, the substitution of a electron-donating group on the para-position of the pyridine ring will promote the LUMO electron density raising the energy level of the vacant states. Either structural modification results in increasing energy of electrons involved in frontier orbital transition $(\pi - \pi^*)$ and an emission that is blue-shifted relative to that of parent Alq₃ (λ_{max}) \sim 514 nm in toluene and 524 in dichloromethane). Although there are several blue or near-blue light-emitting aluminum chelates, Alq₃ derivatives showing deep blue fluorescence (λ_{max}^{f} < 450 nm) have not been realized yet.^{2,6} Surveying literature, we have found that a methyl substituent on the pyridine moiety or aza (nitrogen) replacement of "CH" of the phenoxide moiety of Alq₃ is most attractive in blue-shifting fluorescence color, preserving the rigid and globular structure and good valtility of parent Alq3. Examples are tris(4-methyl-8-quinolinato)aluminum (AlmQ₃) and tris(4-[1,5]naphthyridinolato)aluminum (AlND₃) showing blue-shifted fluorescence at 506 and 440 nm, respectively (Scheme 1). Whereas the greenish AlmQ₃ was reported with EL performance,^{6c-f} application of blue AIND₃ for OLEDs is still literature unknown to date.² Herein, in addition to the 4-hydroxy-1,5-naphthyridine (ND) aluminum chelate, which was efficiently prepared by our improved synthesis, we report the facile synthesis and full characterization of 4-hydroxy-8-methyl-1,5-naphthyridine (mND), 2,8-dimethyl-4-hydroxy-1,5-naphthyridine (mmND), and 4-hydroxy-2-phenyl-1,5-naphthyridine (mpND) metal chelates (Scheme 2). For mND, mmND, and mpND chelating ligands, a whole series of chelates with group III metals (aluminum, gallium, and indium) were also synthesized and characterized. We employ blue-shifting factors of both

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Scheme 1. Chemical Structures of Alq₃, Almq₃, and AIND₃



Scheme 2. Chemical Structures of Group III Metal Chelates of 8-Hydroxy-1,5-naphthyridine Derivatives



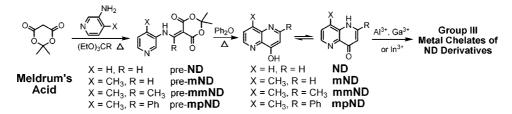
a methyl substituent and aza (nitrogen element) as the replacement of "CH" in one structure. To our surprise, these metal chelates are in fact new substances and previously unknown. In addition to the thermal stability, they were characterized for deep blue fluorescence and EL in applications of OLEDs. Furthermore, due to their wide band gap and electron-deficient nature, we will demonstrate that these metal chelates are feasible as electron-transporting layer (ETL) material, the host material for highly efficient blue fluorescence dopants, or blue host material for yellow dopants to generate white EL in solid state lighting (SSL) applications.

2. Results and Discussion

2.1. Synthesis and Structural Characterization. Parent 4-hydroxy-1,5-naphthyridine (or 1,5-naphthyridin-4-ol) is best known to be prepared by so-called "EMME synthesis" from 3-aminopyridine and diethyl ethoxymethylenemalonate.⁷ After the intramolecular cyclization, the hydrolysis of the resulting ester and thermo-decarboxylation of the acid afford 4-hydroxy-1,5naphthyridine in unsatisfactory overall yields (18–31%).⁸ Alternatively, a shorter and more convenient procedure known as the Cassis method in the synthesis of a wide range of 4-1*H*quinolones (tautomeric forms of hydroxyquinoline) is using

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2,2,6-trimethyl-4*H*-1,3-dioxin-4-one (Meldrum's acid) as an effective diketone equivalent precursor.⁹ Therefore, we adopted the effective Cassis method in the synthesis of the new naphthyrine derivatives, **mND**, **mmND**, and **mpND** (Scheme 3). For comparison purposes in the study herein, parent chelating ligand **ND** was also synthesized by the more convenient Cassis method.

In the first step of synthesis, four pyridylaminomethylene Meldrum's acid derivatives (pre-ND, pre-mND, pre-mmND, pre-mpND) were all obtained in reasonably good yields, 87. 78, 71, and 58%, respectively. Among four species, relatively low yields (58%) of pre-mpND can be attributed to the bulky phenyl group that causes sterical hindrance in the formation of the methylene-bridge-head between the amino substituent and Meldrum's acid. In the following step of a ring closure reaction, heating Meldrum's acid derivatives in diphenyl ether afforded ND, mND, mmND, and mpND in 47-77% yields, respectively. Among them, ND (1,5-naphthyridin-4-ol or 8-hydroxy-1,5naphthyridine) was obtained in lowest yields (47%), and it is due to formation of an undesired structural isomer (1,7naphthyridin-4-ol) in the ring closure reaction. The same cause is believed to occur in the previous "EMME synthesis" of ND, which was prepared in even lower yields.⁸ Nevertheless, the methyl or phenyl substituents of mND, mmND, or mpND are simply from the starting materials of either 3-amino-4-picoline or triethyl orthoacetate/orthobenzoate. A different alkyl group or substituted aromatic ring can be readily incorporated onto ND with appropriate starting materials. Through the case of ND, it is conceivable that the Cassis method illustrated herein is more convenient and versatile. From the Cassis method, we obtained **ND** in $\sim 40\%$ overall synthetic yields, which is in fact better than 18-31% overall synthetic yields from the literature reported "EMME synthesis".8 Moreover, the advantage of the Cassis method is the simpler and more reliable synthetic operation, a two-step procedure instead of a four-step procedure. In "EMME synthesis", a tedious purification process has to be performed four times after each step in the synthetic sequence. The newly synthesized 4-hydroxy-1,5-naphthyridine derivatives were successfully converted into group III metal chelates. However, due to the different reactivity of the metal starting material and the different solubility of the metal chelate product, various reaction conditions and the isolation/purification method were adopted in the final metal chelation reactions, which is somewhat variant from the conventional method preparing Alq₃ (see Experimental Section for details). Basically, the synthesis and purification of hydroxynaphthyridine group III metal chelates are not much difficult than those for the easily prepared and purified Alq₃. They can be readily obtained with volume production in a conventional synthetic laboratory.

These metal chelates were fully characterized by ¹H and ¹³C NMR, mass spectroscopy, and elemental analysis, and they were consistent with proposed structures. Particularly, a single crystal X-ray structure of **AIND**₃ was obtained. Its ORTEP drawing is

displayed in Figure 1.¹⁰ Similar to that of Alq₃, the meridional (*mer*) configuration of AlND₃ is clearly evident by the structure diagram and it is consistent with its complicated ¹H NMR spectrum. Interestingly, unlike AlmND₃ or GamND₃, InmND₃ exhibited a simple ¹H NMR spectrum (four sharp and well-separated proton resonances), an indication of the facial (*fac*) configuration of InmND₃. However, recent evidence has demonstrated that the simple ¹H NMR spectrum of Inq₃ (and hence InmND₃) is due to the rapid fluxional transitions between *mer* and *fac* configurations on the NMR time scale.¹¹

The higher level of electron deficiency of ND than 8-hydroxyquinoline is evident by the significantly smaller pK_a 2.85 of ND than pK_a 5.13 of 8-hydroxyquinoline.¹² ND derivatives have been known for keto-enol tautomerism in polar organic solvents (see Scheme 3).7 We found that the extent of naphthyridone tautomeric forms (and hence the pK_a value) can be gauged by the ¹H NMR signal (chemical shift) of the proton next to the hydroxy substituent of 8-hydroxyquinoline, ND, and mND, which locates at 7.09, 6.52, and 6.50 ppm, respectively (see Figure 2). We expect that even smaller pK_a values are present for **mmND** and **mpND**. The smaller pK_a values (due to the electron deficiency) render ND derivatives weaker δ -donors on the phenoxide side of the chelating ligand. As the result of a weaker δ -donor, the average Al–O bond distance of AlND₃ $(1.867 \pm 0.03 \text{ Å})$ is longer than that $(1.856 \pm 0.02 \text{ Å})$ of Alg₃. On the pyridine side of the chelating ligand, the average Al-N bond distance of AIND₃ (2.025 \pm 0.03 Å) is shorter than that $(2.051 \pm 0.02 \text{ Å})$ of Alq₃, and this can be attributed to the "seesaw-like" binding mode of a bidentate chelating ligand. Otherwise, it can be attributed to the stronger N δ -donor in AIND₃ than in Alq₃ because of the electron-donating methyl substituent *para* to the N δ -donor. We believe that the strength of the δ -donor (or the electron deficiency) of chelating ligands is one of the reasons why aluminum metal chelates of mND, mmND, or mpND all have a shorter fluorescence peak wavelength and are better in blue color purity than AIND3 or Alq₃ (see Table 1 for fluorescence data).

2.2. Photophysical Properties and Energy Levels. Whereas it is the desired deep blue color ($\lambda_{max}^{\text{fl}}$ 415–417 nm) of AlmND₃, AlmmND₃, and AlmpND₃, a less satisfactory sky blue fluorescence ($\lambda_{max}^{\text{fl}}$ 433 nm) of the previously known AlND₃ is clearly shown in their solution fluorescence images (see Figure 3). In the solid state, all four aluminum chelates display redshifted fluorescence wavelength $\lambda_{max}^{\text{fl}}$ 425 nm (AlmpND₃), 431

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⁽¹⁰⁾ Crystal data for **AIND**₃·CH₂Cl₂: C₂₅H₁₇AlCl₂N₆O₃: *Fw* = 547.33, Triclinic, *P*1, *Z* = 2, *F*(000) = 560. Cell dimendions: *a* = 7.9946(7) Å, *b* = 12.0879(11) Å, *c* = 13.1153(12) Å, α = 70.346(2)°, *β* = 82.950(2)°, γ = 84.082(2)°, *V* = 1181.98(18) Å³, 2 θ_{max} = 50.0°, ρ_{cacld} = 1.538 mg/m³. Of 8777 reflections, 4157 were independent, 334 parameters, *R*(*F*₀) = 0.0588 (for reflections with *I* > 2 σ (*I*)), *R*_w(*F*₀) = 0.1663 (for reflections with *I* > 2 σ (*I*)). The GoF on *F*² was 0.977.

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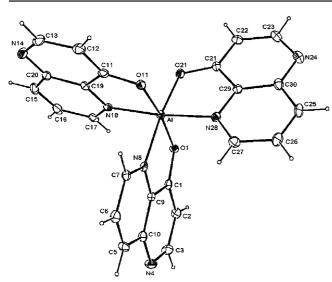


Figure 1. Molecular structure of AIND₃ determined by X-ray diffraction analysis.

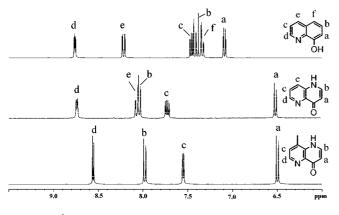


Figure 2. ¹H NMR spectra of 8-hydroxyquinoline, ND, and mND in CD₃OD from top to bottom, respectively.

Table 1. Optical and Thermal Properties of Metal Chelates of 4-Hydroxy-1,5-naphthyridine Derivatives

	solution ^a			solid					
metal chelates	$\lambda_{\max}^{ab}, \lambda_{on set}^{ab}$ (nm)	λ _{max} ^{fl} (nm)	Φ _f (%)	λ_{\max}^{fl} (nm)	Φ _f (%)	T _g (°C)	T₀ (°C)	T _m (°C)	LUMO/HOMO (eV) ^b
Alq ₃	388, 443	524	20	516	40	174	367	412	3.1/5.9
AIND ₃	341, 381	433	47	447	45	122	262	412	-
AlmND ₃	338, 370	415	45	431	43	196	277	420	3.0/6.4
							387		
AlmmND ₃	335, 372	416	45	419	39	233	С	436	-
AlmpND ₃	326, 376	417	45	425	6	204	278	370	-
GamND ₃	341, 374	431	45	439	41	С	С	414	3.2/6.5
GammND ₃	339, 376	432	42	434	52	212	С	430	-
GampND ₃	327, 383	432	25	439	11	185	275	381	-
InmND ₃	344, 382	436	37	445	12	183	С	361	3.3/6.5
InmmND ₃	332, 381	437	36	436	22	221	С	372	-
InmpND ₃	329, 386	437	23	446	8	186	224	370	-

^{*a*} In dichloromethane. ^{*b*} HOMO energy was determined as the edge of HOMO energy level or the ionization potential of the material; LUMO energy was determined as the lowest photoexcitation state energy from the on-set absorption energy in absorption spectra. ^{*c*} Not observed.

nm (AlmND₃), and 447 nm (AlND₃), except $\lambda_{max}^{\text{fl}}$ 419 nm of AlmmND₃ (Table 1). In dichloromethane solution, all four aluminum chelates have reasonably good fluorescence quantum yields (Φ_f) around 45–47% but more or less suffer from fluorescence concentration quenching in the solid state (Table 1).

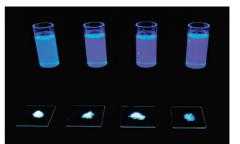


Figure 3. Solution (in dichloromethane) and solid state fluorescence image of AlND₃, AlmND₃, AlmND₃, and AlmpND₃ from left to right, respectively.

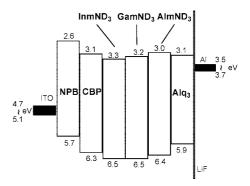


Figure 4. Energy alignment of AlmND₃, GamND₃, InmND₃, Alq₃, NPB, and CBP in OLED devices based on ITO anode and LiF/Al cathode.

Among them, **AlmpND**₃ has the most severe fluorescence quenching in the solid state with a Φ_f of only 6%. Such solidstate fluorescence quenching is universal for **mpND**-based chelates (**AlmpND**₃, **GampND**₃, and **ImmpND**₃. This can be rationalized by the molecular contact (probably $\pi - \pi$ interaction) through protruded phenyl substituents in the solid state. With no exception of the three chelating ligands **mND**, **mmND**, and **mpND**, fluorescence of these metal chelates was observed to be reduced with increasing atomic number of the metal ion from Al to Ga and then In (see Φ_f data in Table 1), known as the heavy atom effect that increases in the rate of intersystem crossing.^{2,13}

In the search for the origin of the wide band gap nature, AlmND₃, GamND₃, and InmND₃ were found to have a HOMO energy level around 6.4-6.5 eV, which is significantly lower than 5.9 eV of Alq₃ (Figure 4). The LUMO energy level of three mND metal chelates is around 3.0-3.3 eV, which is similar to or just a bit lower than 3.1 eV of Alq₃. This is perfectly logical because the prominent electron deficient feature (N aza substituent) locates on the HOMO of the molecule, which is the pyridin-4-olate ring of the chelating ligand, instead of the LUMO of three mND metal chelates, which is the paramethylpyridine (or 4-picoline) ring of the chelating ligand. It can be further identified that either HOMO or LUMO is stabilized by the higher atomic number of the central metals, Al, Ga, and In. Such a stabilization effect happens more prominently in the LUMO than in the HOMO. As a result, the energy band gap of three mND metal chelates decreses in the order AlmND₃ > GamND₃ > InmND₃. Relative to that of Alq₃, a significantly low HOMO energy level and moderately low LUMO energy level enlarge the energy band gap of these hydroxylnaphthyridine-based metal chelates.

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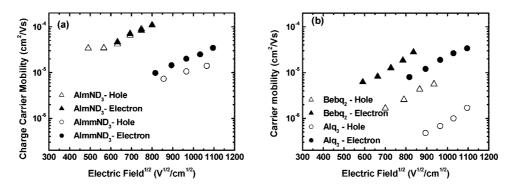


Figure 5. Hole and electron mobility vs the square root of the applied electric field of AlmND₃ and AlmND₃ (a) and Alq₃ and Bebq₂ (b).

2.3. Charge-Transporting Properties and Charge Carrier Mobilities. In terms of HOMO and LUMO energy levels, hydroxynaphthyridine-based metal chelates are better holeblocking or electron-transporting materials than Alq_3 or other deep blue fluorophores. Most known deep blue fluorophores are based on triarylamines, such as NPB, or nonheteroatomcontaining polycyclic aromatic hydrocarbons (PAHs), such as anthracene, perylene, pyrene, or spirobifluorene compounds. Compared with those of hydroxynaphthyridine metal chelates, such nonmetal chelate deep blue fluorophores have significantly higher HOMO and LUMO energy levels of 5.1–5.8 eV and 2.0–2.7 eV (assuming band gap energy is ca. 3.1 eV) below vacuum level, respectively.¹⁴

The HOMO-LUMO energy level of the material shown above is one of the determining factors for electron-transporting or hole-transporting properties of OLED materials. The charge carrier (electron or hole) mobility is the other decisive characteristic that influences the charge-transporting nature and hence the efficiency performance of OLEDs. The relative magnitude of the electron and hole mobility of the material indicates the extent of charge balancing, the efficiency of charge recombination, and hence the EL efficiency of OLEDs. We measured the intrinsic charge carrier (hole or electron) mobility in a bulk film $(0.6-1 \,\mu\text{m})$ of AlmND₃ and AlmmND₃ using the optical timeof-flight (TOF) technique that has been described before. In addition, we also took a measurement on Alq₃ and Bebq₂ with the same measuring system for comparison and accuracy checking. Figure 5 shows the field dependence of the hole and electron drift mobility of AlmND₃, AlmmND₃ (Figure 5a), Alq₃, and Bebq₂ (Figure 5b). First, the electron mobility of Alq₃ was determined to be $\sim 10^{-5}$ cm²/V s at an electric field of 6.4 \times 10⁵ V/cm, which agrees with those obtained previously.¹⁵ Second, the electron mobility of Bebq₂ was determined to be $\sim 10^{-4}$ cm²/V s at the same electric field, which is 1 order of magnitude higher than that of Alq3 and consistent with the report that Bebq₂ is a better electron-transporting material than Alq₃.¹⁶ Devices with an electron-transporting layer (ETL) of Bebq2 have been demonstrated with lower driving voltage and longer operation lifetime, when compared with ones with Alg₃ as an ETL.¹⁶ Third, we found that the charge carrier (either hole or electron) mobility of AlmND₃ is higher than that of AlmmND₃ by nearly 1 order of magnitude (Figure 5a). In fact, checking

the extrapolated data in the range of electric field of $(3.6-6.4) \times 10^5$ V/cm, the charge carrier (either hole or electron) mobility of **AlmND**₃ is the highest among all (Figure 5a and 5b). Therefore, **AlmND**₃ is probably a better electron-transporting material than **AlmmND**₃ because of its high electron mobility. In addition, **AlmND**₃ seems to be the only material that is ambipolar because of its very similar hole and electron mobility determined by TOF technique. On the other hand, **AlmmND**₃ may be a better nondopant deep blue emitter because of its low hole mobility, which limits the amount of hole carrier on **AlmmND**₃ and enhances the charge balance in normally holedominated devices, one crucial factor for high efficiency OLEDs. As shown in the following sections (**2.7** and **2.8**), our OLED results are consistent with the forgoing derivation from the TOF data of **AlmND**₃ and **AlmmND**₃.

2.4. Thermal Properties. Figure 6 shows the differential scanning calorimetry (DSC) thermograms of Alq₃, AIND₃, AlmND₃, GamND₃, AlmmND₃, and GammND₃. In DSC measurements, these metal chelates were first taken from the sample that was purified by a sublimation process. With such prethermal-annealed samples (sublimed-scarped samples), we found that DSC thermograms often show nothing but weak endothermic step transitions, indicative of the glass phase transition temperature (T_g) . To reveal DSC signals of other phase transition temperatures, such as crystallization temperature (T_c) , melting temperature (T_m) , or polymorphic phase transition temperature (T_p) , the sublimed-scarped samples of metal chelates were redissolved in dichloromethane and then evaporated until dryness under reduced pressure at room temperature. In Figure 6, each metal chelate is displayed with two types of DSC traces. First the heating scan, positioned as the top scan, has a heating temperature beyond the large endothermic signal, $T_{\rm m}$. The other scans marked with the sequence number of heating scans or cooling scans in Figure 6 are DSC traces with a measuring temperature less than $T_{\rm m}$, except for AlmpND₃, GampND₃, and InmpND₃ (see Figure S1 for their DSC traces). Two types of heating thermograms were displayed because these metal chelates often exhibit thermal decomposition right after their melting transition, which was evident from observations from a polarized optical microscope (POM). With samples prepared under such conditions, Alq₃ shows T_g (on-set T_g) at 174 °C, a broad and small endortherm peaking at ~355 °C (assigned as $T_{\rm p}$) immediately followed by an exotherm peaked at 367 °C (T_c) , and finally a large endothermic signal at 412 °C (T_m) . Whereas a $T_{\rm g}$ of 174 °C and $T_{\rm m}$ of 412 °C are rather consistent with literature data for Alq₃,^{3c,4,6f,17} the coupled endortherm and

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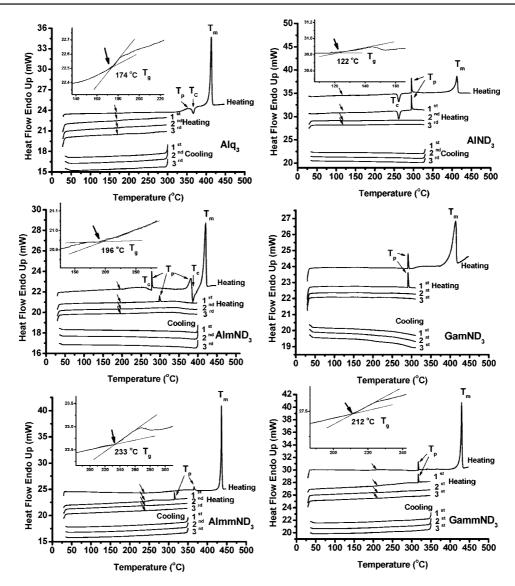


Figure 6. DSC thermograms of Alq₃, AlND₃, AlmND₃, GamND₃, AlmmND₃, and GammND₃.

exotherm have been shown before, although they were reported at higher temperatures of 393 and 396 °C, respectively.^{4,6f,18} It is interesting to know that Alq_3 will be vaporized (sublimed) when heated around melting temperatures at atmospheric pressure.^{6f} We have a similar observation (under POM) for Alq_3 and most metal chelates reported herein as well. Such an observation is indirect evidence that these new metal chelates preserve their superior volatility as well as Alq_3 . Unlike those structurally modified Alq_3 blue derivatives, volatile hydroxynaphthyridine metal chelates reported herein have no problem in the fabrication of OLED by thermal-vacuum-deposition processes.

 Alq_3 has been well-known for its polymorphic and racemic nature and its multiple phase transitions that have been studied

in great detail recently.^{4,6f,18} It has been suggested that the exotherm observed for Alq₃ in DSC traces is due to crystallization, indicative of the instability of the glassy phase of Alq₃. Some new hydroxynaphthyridine metal chelates, such as AlmmND₃, GamND₃, GammND₃, InmND₃, and InmmND₃, show no discernible exotherm in DSC traces, a good sign of the morphological stability of their glassy phase. Except for AIND₃ $(T_{\rm g} \sim 122 \text{ °C})$ and **GamND₃** (no detectable $T_{\rm g}$ in DSC traces), all metal chetates reported herein show $T_{\rm g}$ values around 183-233 °C, which is higher than 174 °C for Alq₃ (Table 1). Higher T_{g} 's of metal chetates often imply a higher morphorlogical stability or a glass phase stability, which is beneficial to the operation lifetime of the multiple-thin-film OLEDs. Furthermore, for all aluminum chelates but AlmpND₃, higher melting temperatures than Alq₃ were observed by DSC (Table 1). This is a plus because the melting transition of these aluminum chelates was rapidly followed by the thermal decomposition. A higher melting temperature means a higher thermal stability in the case of the aluminum chelates studied herein.

Metal chelates based on **mpND** are different from the rest. Among all metal chelates, **AlmpND₃**, **GampND₃**, and **InmpND₃**

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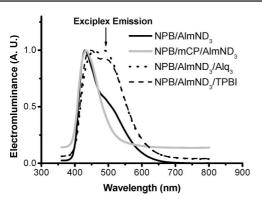


Figure 7. EL spectra of four NPB/AlmND₃-containing OLEDs: ITO/ multiple organic layers/LiF/Al.

were found with relatively low T_g 's of 185–204 °C, and they are easily recognizable in repeated heating scans in DSC measurements (Figure S1). Their T_g 's were always observed prior to a cold crystallization peak without discernible polymorphic phase transition signals (as T_p marked for AIND₃, AImND₃, and AImmND₃ in Figure 6). AImpND₃, GampND₃, and InmpND₃ are also a few exceptions that they do not decompose following the melting transition. Such a difference in thermal properties of mpND-based metal chelates can be all attributed to the protruded phenyl substituent on a symmetric and nearly globular structure of naphthyridinolate metal chelates.

2.5. Elimination of Adverse Exciplex Formation in Non-Doped Blue OLEDs. Deep blue fluorescence of AlmND₃ or AlmmND₃ is very attractive for highly demanding blue OLEDs. A simple nondoped bilayer EL device ITO/NPB(30 nm)/ AlmND₃(30 nm)/LiF(5 nm)/Al (150 nm) was first fabricated by sequential thermal-vacuum-deposition of NPB, AlmND₃, LiF, and Al onto ITO (indium tin oxide)-coated glass substrate. Unfortunately, in addition to the emission band peaking around 430–450 nm of AlmND₃, a pronounced emission band around 480–540 nm appears in the EL spectrum of the device (Figure 7).

Such a long wavelength EL devastates the EL efficiency and also impairs the blue color purity of OLEDs. A similar observation was also found for AlmmND₃ OLEDs. To clarify the origin of the long wavelength EL, three more control devices were then fabricated: ITO/NPB (30 nm)/mCP(30 nm)/ AlmND₃(30 nm)/LiF(5 nm)/Al(150 nm), ITO/NPB(30 nm)/ AlmND₃ (30 nm)/Alq₃(30 nm)/LiF(5 nm)/Al(150 nm), and ITO/ NPB(30 nm)/AlmND₃ (30 nm)/TPBI (30 nm)/LiF (5 nm)/Al (150 nm). From their EL spectra (Figure 7), we can firmly conclude that the EL around 480-540 nm is due to the exciplex emission occurring at the interface of NPB and AlmND₃. It is rather common that electron-deficient materials (such as Alq₃ and 1,3,4-oxadiazole compounds) have a propensity to form exciplex with electron-rich hole-transporting materials (such as NPB triarylamine species).¹⁹ By lowering the HOMO energy level of the hole-transporting material (i.e., reducing the HOMO energy level difference between the hole-transporting material and AlmND₃),^{19d} the problem of the exciplex associated with AlmND₃ can be largely alleviated. As shown in Figure 7, having

Table 2. Electroluminescence Characteristics of Nondoped	
AlmND ₃ OLEDs Containing CBP with Different Layer Thickn	ess ^a

max. luminance, voltage [cd/m ² , V]	luminance, efficiency, voltage [cd/m ² , %, V] ^b	max. efficiency [%, cd/A, lm/W]	λ _{max} el [nm]	CIE 1931 chromaticity [x, y]
5555, 15	119, 0.39, 5.68	0.53, 0.79, 0.33	456	0.18, 0.20
4971, 15	162, 0.86, 5.63	1.08, 1.01, 0.45	450	0.15, 0.11
5070, 15	277, 1.63, 8.37	1.79, 1.51, 0.53	448	0.15, 0.10
5606, 15	315, 1.63, 9.55	1.74, 1.68, 0.53	452	0.16, 0.12
	voltage [cd/m², V] 5555, 15 4971, 15 5070, 15	max. luminance, voltage efficiency, voltage [cd/m², V] cd/m², %, V] ^b 5555, 15 119, 0.39, 5.68 4971, 15 162, 0.86, 5.63 5070, 15 277, 1.63, 8.37	max. efficiency, voltage max. [cd/m², V] voltage [cd/m², %, V] ^b efficiency, [%, cd/A, lm/W] 5555, 15 119, 0.39, 5.68 0.53, 0.79, 0.33 4971, 15 162, 0.86, 5.63 1.08, 1.01, 0.45 5070, 15 277, 1.63, 8.37 1.79, 1.51, 0.53	max. tuminance, voltage efficiency, voltage max. tuminance, efficiency, voltage max. tuminance, efficiency, voltage max. tuminance, efficiency, reficiency [%, cd/A, Im/W] tuminance, efficiency, reficiency [%, cd/A, Im/W] tuminance, reficiency, reficiency [%, cd/A, Im/W] tuminance, reficiency [mm] 5555, 15 119, 0.39, 5.68 0.53, 0.79, 0.33 456 4971, 15 162, 0.86, 5.63 1.08, 1.01, 0.45 450 5070, 15 277, 1.63, 8.37 1.79, 1.51, 0.53 448

^{*a*} Devices have the configuration of ITO/NPB(40 nm)/CBP(x nm)/AlmND₃(30 nm)/Alq₃(20 nm)/LiF(0.5 nm)/Al(150 nm), x = 3, 5, 10, and 15, respectively. ^{*b*} At current density of 20 mA/cm².

a low HOMO energy level around 6.1 eV,²⁰ arylamine mCP (1,3-di(9H-carbazol-9-yl)benzene) is effective in preventing the exciplex emission as evident in device ITO/NPB(30 nm)/ mCP(30 nm)/AlmND₃(30 nm)/LiF(5 nm)/Al (150 nm), although such a device is very poor in EL efficiency and brightness. Also having a low HOMO energy level around 6.3 eV,²¹ another hole-transporting material CBP (4,4'-di(9H-carbazol-9-yl)biphenyl) was thus inserted between NPB and AlmND₃. By the variation of CBP layer thickness, we have successfully eliminated the exciplex emission and optimize the performance of the blue devices ITO/NPB(40 nm)/CBP(x nm)/AlmND₃(30 nm)/ Alq₃ (20 nm)/LiF (5 nm)/Al (150 nm) optimized with x = 10(Table 2). From such CBP-inserted nondoped AlmND₃ OLEDs, we have successfully achieved deep blue ELs ($CIE_{x,y} = 0.15$, 0.10) with a reasonably good external quantum efficiency (η_{ext}) reaching 1.79% (or 1.63% at 20 mA/cm²) and a maximum brightness of 5070 cd/m² (or 277 cd m⁻² at 20 mA/cm²) (Figure 8). To the best of our knowledge, we believe that a similar exciplex problem of AlmND₃ has been found for AlND₃ before and the problem has not been solved until this study.²²

2.6. As Electron-Transporting Material in Non-Doped AlmND₃ OLEDs. Similar to green emitter Alq₃, deep blue emitter AlmND₃ potentially can be used as an electrontransporting material in OLEDs. To gauge such viability, four nondoped AlmND₃ OLEDs containing four different ETL materials were fabricated: ITO/NPB(40 nm)/CBP10 nm)/ AlmND₃(30 nm)/ETL(20 nm)/LiF(5 nm)/Al(150 nm), where the ETL material is TPBI (2,2',2"-(1,3,5-phenylene)tris(1-phenyl-1H-benzimidazole), Bebq₂ (beryllium bis(benzoquinolin-10olate), Alq₃, or AlmND₃. As data have shown in Table 3 and Figure 9, in terms of η_{ext} , nondoped AlmND₃ OLEDs are most efficient when AlmND₃ is employed as the ETL material in OLEDs, although it is not as bright as others. However, in terms of power efficiency ($\eta_{\rm P}$), nondoped AlmND₃ OLEDs having TPBI or $Bebq_2$ are more efficient than ones using Alq_3 or $AImND_3$ as the ETL materials (Table 3). We notice that AlmND₃ provide OLEDs a relatively low current density and a relatively high turn-on voltage (Figure 9), which are comparable with those of Alq₃ but inferor to those of TPBI or Bebq₂. Nevertheless, such results validate the usage of AlmND₃ as an ETL material in OLEDs.

2.7. AIND₃, AlmND₃, AlmmND₃, and AlmpND₃ for High Efficiency Non-Doped Deep Blue OLEDs. Having solved the problem of exciplex EL and demonstrated the electron-

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(d) Matsumoto, N.; Nishiyama, M.; Adachi, C. *J. Phys. Chem. C* **2008**, *112*, 7735.

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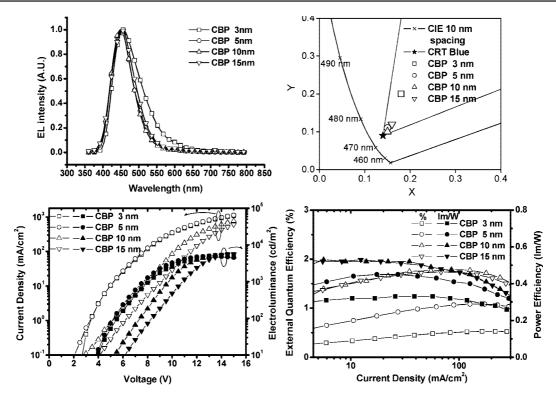


Figure 8. EL characteristics of ITO/NPB(40 nm)/CBP(x nm)/AlmND₃(30 nm)/Alq₃(20 nm)/LiF(0.5 nm)/Al(150 nm), x = 3, 5, 10, and 15, respectively.

Table 3. Electroluminescence Characteristics of Nondoped AImND₃ OLEDs with Various ETL Materials^a

ETL	max. luminance and voltage [cd/m ² , V]	luminance, efficiency, voltage [cd/m ² , %, V] ^b	max. efficiency [%, cd/A, Im/W]	λ _{max} el [nm]	CIE 1931 chromaticity [x, y]
TPBI	6000, 15	240, 1.15, 6.2	1.86, 1.79, 0.86	454	0.16, 0.13
Bebq ₂	7140, 15	340, 1.67, 5.6	1.81, 1.84, 0.98	458	0.15, 0.13
Alq ₃	5070, 15	277, 1.63, 8.4	1.79, 1.51, 0.53	448	0.15, 0.10
AlmND ₃	5240, 15	310, 1.85, 6.8	1.96, 1.65, 0.84	452	0.15, 0.10

^a ITO/NPB(40 nm)/CBP(10 nm)/AlmND₃(30 nm)/ETL(20 nm)/LiF(5 nm)/Al(150 nm). ^b At 20 mA/cm².

transporting property of **AlmND**₃, we are ready to examine and find the best aluminum chelates of **ND**, **mND**, **mmND**, and **mpND** for nondoped deep blue OLEDs. Having **AlmND**₃ as the electron-transporting layer, four nondoped OLEDs were based on **AlND**₃, **AlmND**₃, **AlmmND**₃, and **AlmpND**₃: ITO/ NPB(40 nm)/CBP(10 nm)/Blue Al chelates(30 nm)/**AlmND**₃(20 nm)/LiF(0.5 nm)/Al(150 nm) were fabricated and characterized (Table 4 and Figure 10).

As it can be anticipated from their solution or solid-state fluorescence wavelength, the **AlmND**₃ OLED showed a much deeper blue EL with 1931 Commision Internationale de L'Eclairage *x*, *y* coordinates (CIE_{*x*,*y*} = 0.15, 0.09) than that of **AIND**₃ OLED (CIE_{*x*,*y*} = 0.15, 0.19). However, we do not anticipate that **AlmND**₃ OLED performs better than does **AIND**₃ OLED considering its fluorescence quantum yield. Since fluorescence quantum yields of **AIND**₃ are higher than those of **AlmND**₃ either in solution or in the solid state, we attribute such a result to the charge balancing in the OLED, which has a great influence on the efficiency of the charge-recombination in the OLED. More surprisingly, the **AlmmND**₃ OLED shows the shortest EL wavelength ($\lambda_{max}^{EL} \sim 436$ nm), the highest η_{ext} of 4.18% (or 4.11% at 20 mA/cm²), and the brightest EL of 445 cd/m² at 20 mA/cm². Considering the structural difference among **AIND**₃, **AlmND**₃, and **AlmmND**₃, it is hard to conceive

that an insignificant methyl substituent or the number of methyl substituents can exert that much on η_{ext} and EL brightness. Plausibly, among four aluminum chelates, we may recognize AlmmND₃ as an exceptional one based on the red-shifted fluorescence from solution to the solid state. The red-shifting fluorescence is 443→447 nm, 415→431 nm, 416→419 nm, and 417→425 nm for AIND₃, AlmND₃, AlmmND₃, and AlmpND₃, respectively. Energywise, this corresponds to a red-shifting energy of 723, 895, 172, and 451 cm⁻¹, respectively for four aluminum chelates. AlmmND₃ has the smallest red-shifted fluorescence among all. Accordingly, we surmise that, in the solid state, AlmmND₃ aggregates in a quite different fashion from the other aluminum chelates. Compared with other aluminum chelates, such aggregation enables high efficiency of charge recombination (or charge balance) and thus the η_{ext} (or $\eta_{\rm P}$) of AlmmND₃ OLEDs. For AlmmND₃, the low hole mobility (lower than its electron mobility) helps in balancing the charge of AlmmND₃ OLEDs.

We have also examined the performance of blue OLEDs with **GamND₃**, **GammND₃**, **InmND₃**, or **InmmND₃** as the nondoped light-emitting layer (Table S1). As it can be anticipated from the fact that a heavy atom will quench the fluorescence, indium chelates performed the worst in terms of EL efficiency or brightness. However, this is not exactly the case for gallium chelates. Comparing data in Table 4 and Table S1, the **GammND₃** OLED is worse than the **AlmmND₃** OLED but the **GamND₃** OLED is better than the **AlmND₃** OLED. Nevertheless, once again, we verified the same trend of OLED performance; namely, **mmND** is better than **mND** for gallium or indium metal chelates as nondoped deep blue light-emitting materials for OLEDs.

2.8. Nondoped AlmmND₃ OLEDs with Various Metal Chelates as Electron-Transporting Layer. Knowing all group III metal chelates are potential ETL material in OLEDs, we fabricated a series of **AlmmND₃**-based nondoped blue OLEDs

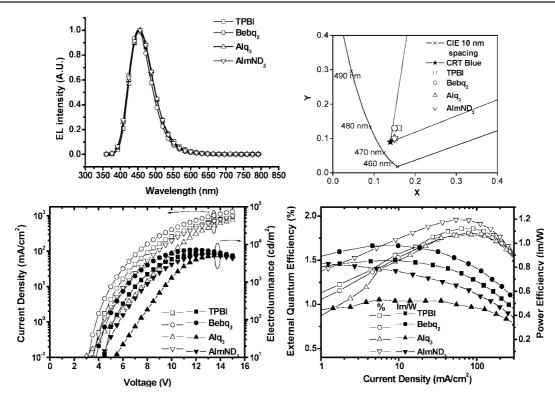


Figure 9. EL characteristics of ITO/NPB(40 nm)/CBP(10 nm)/AlmND₃(30 nm)/ETL(20 nm)/LiF(0.5 nm)/Al(150 nm), where ETL is TPBI, Bebq₂, Alq₃, and AlmND₃, respectively.

Table 4. Electroluminescence Characteristics of Nondoped OLEDs of AIND₃, AImND₃, AImND₃, and AImpND₃ blue AI chelates^a

Al chelates	max. luminance and voltage [cd/m ² , V]	luminance, efficiency, voltage [cd/m ² , %, V] ^b	max. efficiency [%, cd/A, lm/W]	λ _{max} el [nm]	CIE 1931 chromaticity [<i>x</i> , <i>y</i>]
AlND ₃ AlmND ₃ AlmmND ₃ AlmpND ₃	2286, 15 3824, 15 3792, 15 4078, 15	445, 4.11, 9.36	1.91, 1.43, 0.77	448 436	0.15, 0.09 0.15, 0.07

^{*a*} Devices have the configuration of ITO/NPB(40 nm)/CBP(10 nm)/ Blue Al chelates(30 nm)/AlmND₃(20 nm)/LiF(0.5 nm)/Al(150 nm). ^{*b*} At current density of 20 mA/cm².

with a variation of ETL material, AIND₃, AlmND₃, AlmMND₃, AlmpND₃, GamND₃, or InmND₃ (Table 5 and Figure S2). Here, for a fair comparison, the AlmmND₃ OLED having AlmND₃ as ETL material is a refabricated one, not the same one in Table 4 and Figure 10. As the data show in Table 5, all devices exhibit virtually the same λ_{max}^{el} 432 nm and a very similar deep blue color chromaticity $CIE_{x,y} = 0.15 - 0.16$, 0.07-0.08, consistent with all OLEDs having the same deep blue nondoped emitter AlmmND₃. Regardless of ETL materials, all deep blue OLEDs have a relatively high EL efficiency with η_{ext} being more than 3.0%. In terms of EL efficiency, the AlmmND₃ OLED having AlmND₃ as the ETL material is the most outstanding. This OLED has η_{ext} reaching 3.77% and η_{P} over 0.80 lm/W at a current density of 20 mA/cm². From OLED results in section 2.7 and 2.8, it is very clear that AlmmND₃ is the most efficient nondoped deep blue emitter but AlmND₃ is the best ETL material for it.

2.9. AlmND₃ as the Host Material for Blue Perylene and Deep Blue 9,10-Diphenylanthracene Dopants. To demonstrate the wide band gap nature of hydroxynaphthyridine metal chelates, we have fabricated a series of AlmND₃ OLEDs containing perylene or 9,10-diphenylanthracene (DPA) as highly efficient blue or deep blue dopant materials. Perylene is a highly

fluorescent blue emitter with $\lambda_{\max}^{\text{fl}}$ 467 nm (in clyclohexane) and Φ_f 94%.²³ However, in the solid state blue perylene becomes a poor fluorophore, a yellow one, due to the severe molecular aggregation that brings about concentration quenching, and a diminished and red-shifting fluorescence takes place. The fluorescence of DPA is even bluer and stronger showing $\lambda_{\max}^{\text{fl}}$ 438 nm (in cyclohexane) and Φ_f 100%.²³ Similar to blue perylene, deep blue DPA has the inherent problem of crystallizing when deposited as a thin film that prohibits its nondopant usage in a device.²⁴ Whereas some reports are available for the dopant usage of perylene,²⁵ there is no known literature case of the dopant usage of DPA in OLEDs to date. This can be simply attributed to the lack of appropriate host material, a wide band gap one, required for such a deep blue DPA dopant.

We took 0.5, 2, and 4 wt % dopant concentration of both perylene and DPA in the fabrication of dopant-based **AlmND**₃ OLEDs. The EL characteristics of both series of devices are displayed in Figures 11 and 12, and their data are summarized in Table 6.

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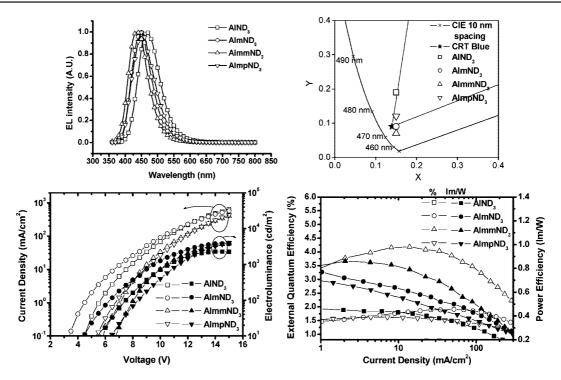


Figure 10. EL characteristics of ITO/NPB(40 nm)/CBP(10 nm)/Blue Al chelate(30 nm)/ETL(20 nm)/LiF(0.5 nm)/Al(150 nm), where Blue Al chelate is AlND₃, AlmND₃, AlmND₃, and AlmpND₃, respectively.

Table 5. Electroluminescence Characteristics of Nondoped OLEDs of AlmmND₃ with Various Metal Chelates as ETL Materials^{*a*}

ETL	max. luminance and voltage [cd/m ² , V]	luminance, efficiency, voltage [cd/m ² , %, V] ^b	max. efficiency [%, cd/A, lm/W]	λ _{max} ^{el} [nm]	CIE 1931 chromaticity [x, y]
AIND ₃ AlmND ₃ AlmmND ₃ AlmpND ₃ GamND ₃ InmND ₃	3313, 15 4444, 15 4879, 15 5487, 15 4694, 15 3848, 15	369, 3.40, 8.92 401, 3.77, 7.75 329, 3.01, 8.60 376, 3.23, 8.24 416, 3.67, 8.18 376, 3.62, 8.62	3.67, 2.00, 1.04 3.79, 2.00, 0.94 3.27, 1.78, 0.84 3.41, 1.99, 1.13 3.68, 2.09, 0.93 3.67, 1.91, 0.91	432 432 432 432	0.15, 0.07

^{*a*} Devices have the configuration of ITO/NPB(40 nm)/CBP(10 nm)/ AlmmND₃(30 nm)/ETL(20 nm)/LiF(0.5 nm)/Al(150 nm). ^{*b*} At current density of 20 mA/cm².

Dopant concentration 0.5 wt% was found to be optimum for either perylene or DPA. The vibronic emission observed at the low energy side of the major EL band is the distinct feature of a not so blue preylene EL, indicating a sufficient Förster energy transfer between the AlmND₃ host and perylene dopant. Compared to the undoped device (second entry of Table 4), the maximum EL efficiency of the perylene-doped device was enhanced more than four times to \sim 3.06 lm/W, or more than three times to \sim 4.67 cd/A. At a current density of 20 mA/cm², η_{ext} was 3.13%, which was enhanced 1.7 times compared to an undoped device. The maximum electroluminance also increased to 12 420 cd/m², a greater than 3-fold enhancement than that of the undoped device, although this is at a price of deep blue color purity. The perylene-doped device had a chromaticity of $CIE_{x,y} =$ 0.14, 0.17, less deep blue than $CIE_{x,y} = 0.15$, 0.09 of the undoped device (second entry of Table 4). Nonetheless, the performance of the 0.5 wt% perylene-doped AlmND₃ OLED reported herein is one of the best perylene dopant devices known in literature.²⁵ Similar enhancement of the OLED performance was also observed for DPA-doped devices, although the enhancement was to a smaller extent when compared with that of perylene-doped OLEDs. However, the

deep blue color purity was elevated to a higher level, $\text{CIE}_{x,y} = 0.15$, 0.06. After the comparison with emission spectra of solution DPA, solid state **AlmND**₃, and solid state DPA (fluorescence spectra shown in Figure 12), the EL spectra of the DPA-doped **AlmND**₃ OLED can be recognized as a coemission from both DPA and **AlmND**₃. Since the main emission wavelength of DPA is shorter than that for **AlmND**₃, the coemission EL observed for the DPA-doped **AlmND**₃ OLED gave rise to the deepest blue color (see inserted 1931 CIE chromaticity diagram in Figure 12). Considering the inadequate overlapping of the absorption spectrum of DAP and the emission spectrum of **AlmND**₃ (not shown in Figure 12), we can conceive that Förster energy transfer between

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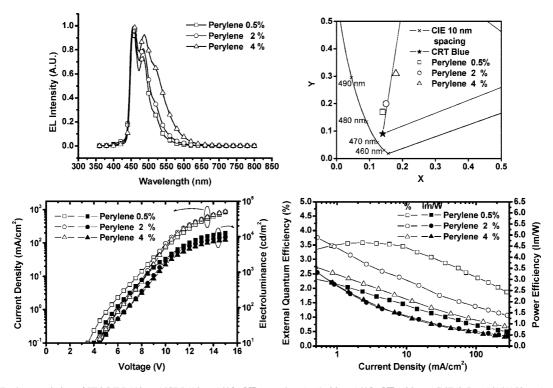


Figure 11. EL characteristics of ITO/NPB(40 nm)/CBP(10 nm)/AlmND₃:perylene(x %, 30 nm)/AlmND₃(20 nm)/LiF(0.5 nm)/Al(150 nm), where x is 0.5, 2, or 4, the weight percent of perylene dopant.

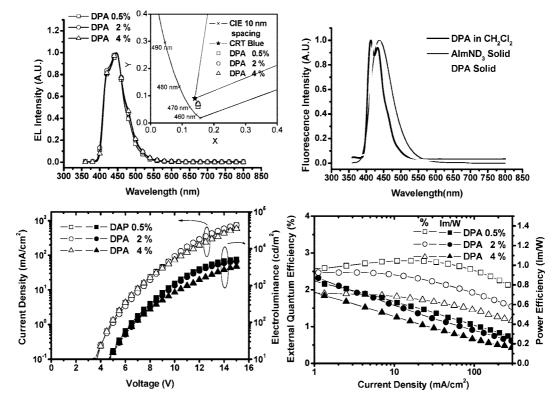


Figure 12. EL characteristics of ITO/NPB(40 nm)/CBP(10 nm)/AlmND₃:DPA(x %, 30 nm)/AlmND₃(20 nm)/LiF(0.5 nm)/Al(150 nm), where x is 0.5, 2, or 4, the weight percent of DPA dopant

the **AlmND**₃ host and DPA dopant is somewhat incomplete, even though the HOMO energy level of the **AlmND**₃ host is low enough for the DPA dopant (but the LUMO energy level of **AlmND**₃ is not high enough for the DPA dopant). Despite such a coemission, to the best of our knowledge, this is the first observation of a deep blue EL from DPA. **2.10.** AlmND₃ as the Host Material for High Efficiency White OLEDs with Rubrene Yellow Dopant. Yellow fluorophore rubrene is probably the most commonly used dopant accompanying blue fluorescent host material in the fabrication of white OLEDs.^{26,27} Fluorescence spectrum of AlmND₃ is partially overlapping with the absorption spectrum of rubrene

Table 6. Electroluminescence Characteristics of **AImND**₃ OLEDs with Various Dopant (Perylene or 9,10-Diphenylanthracene) Concentrations^{*a*}

dopant concn [wt %]	max. luminance and voltage [cd/m ² , V]	luminance, efficiency, voltage [cd/m ² , %, V] ^b	max. efficiency [%, cd/A, lm/W]	λ _{max} ^{el} [nm]	CIE 1931 chromaticity [<i>x</i> , <i>y</i>]
		Perylene as	Dopant		
0.5	12420, 15	810, 3.13, 8.3	3.56, 4.67, 3.06	456	0.14, 0.17
2	9610, 15	590, 1.98, 8.7	3.77, 3.51, 3.28	456	0.15, 0.20
4	8060, 15	580, 1.38, 8.9	2.73, 5.45, 3.69	458	0.18, 0.31
	9,10-E	Diphenylanthrace	ne (DPA) as Dopa	nt	
0.5	5120, 15	278, 2.78, 5.8	2.80, 1.39, 0.89	448	0.15, 0.06
2	4595, 15	259, 2.31, 5.4	2.47, 1.38, 0.87	446	0.15, 0.07
4	3295, 15	203, 1.75, 5.6	1.90, 1.91, 0.69	446	0.18, 0.07

^{*a*} ITO/NPB(40 nm)/CBP(10 nm)/AlmND₃:Dopant (x %, 30 nm)/AlmND₃(20 nm)/LiF(5 nm)/Al(150 nm), where x = 0.5, 2, and 4 (weight percent) for perylene or 9,10-diphenylanthracene (DPA) dopant. ^{*b*} At 20 mA/cm².

(Figure S3 left), and white fluorescence is feasible with an appropriate ratio of mixed **AlmND**₃ and rubrene (Figure S3 right).

We have demonstrated that the deep blue **AlmND**₃ is a good host material for rubrene in generating high EL efficiency white OLEDs. A series of OLEDs ITO/NPB(40 nm)/CBP(10 nm)/ **AlmND**₃:rubrene(x %, 30 nm)/**AlmND**₃(20 nm)/LiF(0.5 nm)/ Al(150 nm) with a variation of rubrene dopant concentration 0.5–4 wt% and EL characteristics of such **AlmND**₃:rubrene OLEDs are shown in Figure 13 and their data are summarized in Table 7.

Similar to most rubrene-based white OLEDs, an authentic white color purity (CIE_{x, y} = 0.32, 0.38) was achieved at a very low dopant concentration, 0.5 wt % of AlmND₃ (first entry of Table 7). Any higher dopant concentration simply impairs the white color purity of OLEDs. For such white OLEDs at a brightness of 100 cd/m², η_{ext} is 4.25%, which is equivalent to an η_P of 8.67 lm/W, one of the highest among literature-known rubrene-based white OLEDs.^{26,27} The color rendering index (CRI) of such white (two-color-component) OLEDs was determined to be in the range 45-50, and it is in general inferior to CRI \sim 80 of three-color-component white OLEDs.²⁸ At practical lighting conditions, i.e., 1000 cd/m², such an AlmND₃: rubrene white OLED has an η_{ext} of ~3.9% or η_{P} of 5.1 lm/W (Figure 13). With few exceptions,²⁷ this EL efficiency at 1000 cd/m² also outperforms most literature-known rubrene-based two-element white OLEDs. Also, a doped device with a 4% rubrene concentration is virtually a yellow OLED, $CIE_{x, y} =$ 0.45, 0.51 (Figure 13 and the fourth entry of Table 7). Its high efficiency, 4.56%, 15.83 cd/A, or 11.94 lm/W, at 100 cd/m² and high brightness (1930 cd/m² at 20 mA/cm²) outperforms most currently known yellow OLEDs.²⁹ The high EL efficiency of such rubrene-based white or yellow OLEDs can be attributed to the high electron mobility of AlmND₃. High electron mobility is rarely observed for the host material in the white or yellow

OLEDs, and it facilitates the charge balance and hence the EL efficiency of OLEDs.

3. Conclusion

We have reported the first series of group III metal chelates as the authentic deep blue analogues of green Alq₃. A large quantity of these deep blue metal chelates are readily available now due to our improved synthesis and facial purification method applicable for them. Unlike several currently known blue analogues of Alq₃, these deep blue group III metal chelates are volatile and thermally stable enough for OLED fabrication by a vacuum-thermal-deposition process. For OLEDs, we have overcome the problem of exciplex formation, which has hampered AIND₃ from practical usage in OLEDs before. High efficiency (maximum $\eta_{ext} > 4.0\%$) and deep blue (CIE_{x,y} = 0.15, 0.07) nondoped OLEDs were achieved for AlmmND₃. The wide band gap of these deep blue metal chelates, 6.4 and 3.0 eV for AlmND₃ HOMO and LUMO energy levels, respectively, enable their usage as the host material for perylene blue dopant or deep blue 9,10-diphenylanthracene. These group III metal chelates, particularly AlmND₃ and AlmmND₃, have been characterized for the charge carrier mobility by a time-of-flight technique. Both AlmND₃ and AlmmND₃ exhibit high electron mobility, comparable with or even higher than that of BeBq₂ or Alq₃. Moreover, **AlmND**₃ is ambipolar with a similar mobility of 10^{-4} cm²/Vs for both hole and electron. The success of highly efficient white OLEDs (or yellow OLEDs) based on a rubrene dopant is attributed to the high electron (and hole) mobility of the host material, AlmND₃. We have demonstrated the versatile and effective application of hydroxynaphthyridine-based group III metal chelates for OLEDs. More high performance OLEDs can be anticipated now due to the availability of long-thought, wide band gap, deep blue group III metal chelates.

4. Experimental Section

General Information. Both solution and solid-state fluorescence quantum yields (Φ_f 's) of the blue metal chelates were determined by the integrating-sphere method.³⁰ Photoluminescence (PL) spectra were recorded on a Hitachi fluorescence spectrophotometer F-4500, and the same spectrophotometer was used to record the EL spectra of OLEDs. Melting points ($T_{\rm m}$ s), glass transition temperatures ($T_{\rm g}$'s), and crystallization temperatures $(T_c's)$ of respective compounds were measured via differential scanning calorimetry (DSC) using a Perkin-Elmer DSC-6 differential scanning calorimeter. The HOMO energy levels of the thin-film samples of metal chelates were studied by ultraviolet photoemission spectroscopy (UPS). The experimental detail of UPS measurement has been described before.³¹ LUMO energy levels were estimated by subtracting the energy gap (ΔE) from HOMO energy levels. ΔE was determined by the on-set absorption energy from the absorption spectra of the materials. UV-visible electronic absorption spectra were recorded on a Hewlett-Packard 8453 Diode Array spectrophotometer. The method of time-of-flight (TOF) in measuring charge carrier mobility has been reported before.³² Data collection of the X-ray crystallography analysis was carried out on a Brucker X8APEX CCD

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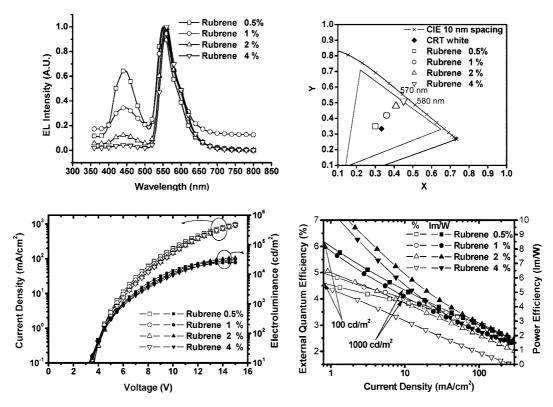


Figure 13. EL characteristics of ITO/NPB(40 nm)/CBP(10 nm)/AlmND₃:rubrene (x %, 30 nm)/AlmND₃ (20 nm)/LiF(0.5 nm)/Al(150 nm), where x is 0.5, 1, 2, or 4, the weight percent of rubrene dopant. EL efficiency (η_{ext} or η_P) at 100 or 1000 cd/m² electroluminance is arrow-marked for the device with 0.5 wt% rubrene dopant.

Table 7. Electroluminescence Characteristics of White OLEDs with AImND₃ Host and Various Dopant (Rubrene) Concentration^a

rubrene concn [wt %]	max. luminanceand voltage [cd/m², V]	luminance, efficiency, voltage [cd/m², %, V] ^b	efficiency at 100 and 1000 cd/m ² [%, cd/A, Im/W]	$\lambda_{\sf max}^{\sf el}$ [nm]	CIE 1931 chromaticity [<i>x</i> , <i>y</i>]
0.5	26 710, 15	1830, 3.67, 6.58	4.25, 11.55, 8.67 3.91, 9.65, 5.13	444, 550	0.30, 0.35
1	24 810, 15	1670, 3.73, 6.75	4.97, 11.17, 8.20 3.97, 8.93, 4.58	444, 554	0.36, 0.42
2	36 290, 15	2260, 3.47, 7.02	5.35, 17.46, 13.03 3.98, 12.97, 6.78	444, 558	0.41, 0.48
4	30 970, 15	1930, 2.79, 7.05	4.56, 15.83, 11.94 3.24, 11.25, 5.77	444, 560	0.45, 0.51

^{*a*} Devices have the configuration of ITO/NPB(40 nm)/CBP(10 nm)/AlmND₃:rubrene x %(30 nm)/AlmND(20 nm)/Al(150 nm), x = 0.5,

1, 2, 4, respectively. ^b At current density of 20 mA/cm.

diffractometer at 100 K for AIND₃•CH₂Cl₂ single crystals. The experimental detail of X-ray diffraction and their data process in solving the crystal structure can be found elsewhere.^{30b}

The fabrication of OLEDs and their EL characterization also have been described before.^{19b,33} The device was placed close to the photodiode such that all the forward light entered the photodiode. The effective size of the emitting diodes was 3.14 mm², which is significantly smaller than the active area of the photodiode dectector, a condition known as "under-fillling", satisfying the measurement protocol.³⁴ This is one of the most conventional ways in measuring the EL efficiency of OLEDs, although sometimes experimental errors may arise due to the non-Lambertian emission of OLEDs.³⁵ The color rendering index (CRI) of white OLEDs was measured by a spectroradiometer (Specbos 1201, JETI Technishe Instrumente GmbH). ¹H and ¹³C NMR specra were recorded on a Bruker AMX-400 MHz or AVA-400 MHz Fourier-transform spectrometer at room temperature. Elemental analyses (on a Perkin-Elmer 2400 CHN Elemental Analyzer) and electron impact (EI), fast atom bombardment (FAB), or matrix-assisted laser desorption/ionization timeof-flight (MALDI-TOF) mass spectra (on a VA Analytical 11-250J or 4800 MALDI TOF/TOF Analyzer) were recorded by the Elemental Analyses and Mass Spectroscopic Laboratory in-house service of the Institute of Chemistry, Academic Sinica.

Materials. For the materials used in device fabrication, Bebq₂, DPA (9,10-diphenylanthracene), perylene, and rubrene are commercially available materials and they were used without further purification. NPB (1,4-bis(1-naphthylphenylamino)biphenyl), CBP (4,4'-bis(9-carbazolyl)-2,2'-biphenyl), *m*CP (1,3-bis(9-carbazolyl)-benzene), TPBI (2,2',2''-(1,3,5-phenylene)tris[1-phenyl-1*H*-benz-imidazole]), and **Alq₃** were prepared via published methods and were subjected to gradient sublimation prior to use.

Synthesis of Tris(4-hydroxy-1,5-naphthyridinato)aluminum (AlND₃). To a toluene solution (4.5 mL) was added ND (0.15 g, 1.0 mmol) and aluminum triisopropoxide (0.07 g, 0.34 mmol). The

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reaction mixture was heated at reflux under nitrogen for 1 h. During the reaction, a formation of milky white solid emitting blue fluorescence was observed. After cooling, the reaction solution was filtered to isolate a white solid. After washing with *n*-hexanes, the solid was subjected to zone-temperature sublimation. The pure product was isolated as a white solid. Yield: 76% (0.12 g). ¹H NMR (400 MHz, CD_2Cl_2): δ 8.77 (d, 1H, J = 4.75 Hz), 8.73–8.67 (m, 4H), 8.56 (d, 1H, J = 8.54 Hz), 8.51–8.47 (m, 2H), 7.73 (dd, 1H, J = 8.56 Hz, J = 4.72 Hz), 7.56 (dd, 1H, J = 8.60 Hz, J = 4.75Hz), 7.49 (dd, 1H, J = 8.50 Hz, J = 4.74 Hz), 7.29 (d, 1H, J =4.59 Hz), 6.93 (d, 1H, J = 5.33 Hz), 6.90 (d, 1H, J = 5.34 Hz). 6.81 (d, 1H, J = 5.32 Hz). ¹³C NMR (100 MHz, CDCl₃): δ 165.17, 164.98, 164.65, 156.28, 155.73, 155.70, 144.80, 144.43, 144.17, 144.07, 142.39, 141.87, 141.45, 141.37, 138.84, 138.18, 138.01. 125.13, 124.55, 109.80, 109.62, 109.08. FAB-MS: calcd 462.10, $m/z = 463.1 \text{ (M+H^+)}$. Anal. Found (Calcd) for C₂₄H₁₅AlN₆O₃: C₃₄H₁₅AlN₆O₃: C₃₄H₁₅AlN 62.31 (62.34); H, 2.93 (3.27); N, 17.88 (18.17).

Synthesis of Tris(4-hydroxy-8-methyl-1,5-naphthyridinato)aluminum (AlmND₃). This compound was synthesized in the same manner as AlND₃, except that mND (1.00 g, 6.2 mmol) was used instead of ND. The pure product was isolated as a white solid. Yield: 86% (0.90 g). ¹H NMR (400 MHz, CDCl₃): δ 8.73–8.70 (m, 3H), 8.57 (d, 1H, *J* = 4.90 Hz), 8.52 (d, 1H, *J* = 4.91 Hz), 7.51 (d, 1H, *J* = 4.81 Hz), 7.42 (d, 1H, *J* = 4.90 Hz), 7.27 (d, 1H, *J* = 4.76 Hz), 7.11 (d, 1H, *J* = 4.94), 6.94 (d, 1H, *J* = 5.34 Hz), 6.91 (d, 2H, *J* = 5.34 Hz), 2.84 (s, 3H), 2.79 (s, 3H), 2.77 (s, 3H). ¹³C NMR (100 MHz, CDCl₃): δ 165.58, 165.44, 165.12, 154.74, 154.22, 154.20, 153.22, 152.70, 152.56, 143.95, 143.76, 143.70, 143.65, 143.62, 141.75, 137.99, 137.31, 137.18, 125.25, 125.23, 124.69, 109.68, 109.40, 108.91, 17.76, 17.67. FAB-MS: calcd 504.15, *m*/*z* = 505.1 (M+H⁺). Anal. Found (Calcd) for C₂₇H₂₁AlN₆O₃: C, 64.20 (64.28); H, 4.33 (4.20); N, 16.36 (16.66).

Synthesis of Tris(4-hydroxy-2,8-dimethyl-1,5-naphthyridinato)aluminum (AlmmND₃). This compound was synthesized in the same manner as AlND₃, except that mmND (0.50 g, 2.9 mmol) was used instead of ND. The pure product was isolated as a white solid. Yield: 86% (0.45 g). ¹H NMR (400 MHz, CDCl₃): δ 8.46 (d, 1H, *J* = 4.88 Hz), 8.43 (d, 1H, *J* = 4.88 Hz), 7.42 (d, 1H, *J* = 4.88 Hz), 7.34 (d, 1H, *J* = 4.88 Hz), 7.18 (d, 1H, *J* = 4.92 Hz), 7.00 (d, 1H, *J* = 4.96 Hz), 6.81 (s, 2H), 6.80 (s, 1H), 2.80 (s, 3H), 2.76 (s, 3H), 2.74 (s, 3H), 2.61 (s, 3H), 2.60 (s, 6H). ¹³C NMR (100 MHz, CDCl₃): δ 165.03, 164.76, 164.24, 163.59, 152.01, 151.57, 151.40, 143.09, 143.05, 142.99, 142.74, 142.48, 140.61, 136.89, 136.23, 136.09, 125.08, 124.60, 109.67, 109.26, 108.89, 26.36, 26.29, 17.60, 17.53. FAB-MS: calcd 546.20, *m*/*z* = 547.2 (M+H⁺). Anal. Found (Calcd) for C₃₀H₂₇AlN₆O₃: C, 65.54 (65.93); H, 4.94 (4.98); N, 15.37 (15.38).

Synthesis of Tris(4-hydroxy-8-dimethyl-2-phenyl-1,5-naphthyridinato)aluminum (AlmpND₃). This compound was synthesized in the same manner as AlND₃, except that mpND (0.20 g, 0.9 mmol) was used instead of ND. The pure product was isolated as a white solid. Yield: 77% (0.16 g). ¹H NMR (400 MHz, *d*₆-DMSO): δ 8.59 (d, 1H, *J* = 4.90 Hz), 8.49 (d, 1H, *J* = 4.92 Hz), 8.23–8.20 (m, 6H), 7.78 (d, 1H, *J* = 5.00 Hz), 7.69 (d, 1H, *J* = 4.91 Hz), 7.58–7.42 (m, 14H), 2.85 (s, 3H), 2.83 (s, 3H), 2.80 (s, 3H). ¹³C NMR (100 MHz, CDCl₃): δ 165.79, 165.75, 165.51, 161.48, 161.04, 153.20, 152.82, 152.69, 143.43, 143.32, 143.12, 141.23, 140.46, 140.25, 139.94, 137.32, 136.68, 136.52, 129.65, 129.46, 129.29, 128.71, 128.67, 128.60, 127.72, 127.65, 127.62, 125.39, 124.88, 17.55, 17.47. FAB-MS: calcd 732.24, *m/z* = 733.3 (M+H⁺). Anal. Found (Calcd) for C₄₅H₃₃AlN₆O₃: C, 73.84 (73.76); H, 4.37 (4.54); N, 11.37 (11.47).

Synthesis of Tris(4-hydroxy-8-methyl-1,5-naphthyridinato)gallium (GamND₃). To a water solution (7.2 mL) were added mND (0.14 g, 0.87 mmol) and gallium chloride (0.06 g, 0.34 mmol). The reaction mixture was heated and stirred at \sim 40 °C. An excess amount of potassium acetate was added to the solution to change the solution acidity from pH 3–4 to pH 7–8. During the reaction (ca. 1 h), the formation of a milky white solid emitting blue fluorescence was observed. After cooling, the reaction solution was filtered to isolate the white solid. After washing with water, the solid was vacuum-dried and finally subjected to zone-temperature sublimation. The pure product was isolated as a white solid. Yield: 67% (0.11 g). ¹H NMR (400 MHz, CDCl₃): δ 8.70 (d, 3H, *J* = 5.36 Hz), 8.62 (d, 1H, *J* = 4.83 Hz), 8.57 (d, 1H, *J* = 4.90 Hz), 7.54 (d, 1H, *J* = 4.80 Hz), 7.46 (d, 1H, *J* = 4.71 Hz), 7.31 (d, 1H, *J* = 4.78 Hz), 7.27 (d, 1H, *J* = 4.89), 6.96 (d, 1H, *J* = 5.37 Hz), 6.93 (d, 1H, *J* = 5.42 Hz), 6.92 (d, 1H, *J* = 5.36 Hz), 2.84 (s, 3H), 2.80 (s, 3H), 2.78 (s, 3H). ¹³C NMR (100 MHz, CDCl₃): δ 165.18, 164.98, 164.74, 154.43, 153.96, 153.51, 153.04, 153.00, 143.89, 143.81, 143.41, 143.15, 141.22, 136.08, 135.45, 135.34, 125.23, 125.14, 124.71, 109.61, 109.51, 108.97, 17.95, 17.85. FAB-MS: calcd 546.09, *m/z* = 547.0 (M+H⁺). Anal. Found (Calcd) for C₂₇H₂₁GaN₆O₃: C, 59.03 (59.26); H, 4.00 (3.87); N, 15.09 (15.36).

Synthesis of Tris(4-hydroxy-2,8-dimethyl-1,5-naphthyridinato)gallium (GammND₃). This compound was synthesized in the same manner as **GamND**₃, except that **mmND** (0.60 g, 3.4 mmol) was used instead of **mND**. The pure product was isolated as a white solid. Yield: 83% (0.56 g). ¹H NMR (400 MHz, CDCl₃): δ 8.51 (d, 1H, *J* = 4.83 Hz), 8.48 (d, 1H, *J* = 4.86 Hz), 7.45 (d, 1H, *J* = 4.78 Hz), 7.38 (d, 1H, *J* = 4.90 Hz), 7.23 (d, 1H, *J* = 4.89 Hz), 7.15 (d, 1H, *J* = 4.90 Hz), 6.83–6.82 (m, 3H), 2.80 (s, 3H), 2.77 (s, 3H), 2.75 (s, 3H), 2.61 (s, 3H), 2.59 (s, 6H). ¹³C NMR (100 MHz, CDCl₃): δ 164.63, 164.56, 164.36, 163.94, 163.40, 163.33, 152.32, 151.88, 143.31, 143.25, 142.20, 142.00, 140.07, 135.02, 134.38, 134.26, 125.10, 124.96, 124.62, 109.57, 109.32, 108.88, 26.31, 17.80, 17.71. FAB-MS: calcd 588.14, *m/z* = 589.0 (M+H⁺). Anal. Found (Calcd) for C₃₀H₂₇GaN₆O₃: C, 61.50 (61.14); H, 4.63 (4.62); N, 14.17 (14.26).

Synthesis of Tris(4-hydroxy-8-dimethyl-2-phenyl-1,5-naphthyridinato)gallium (GampND₃). This compound was synthesized in the same manner as GamND₃, except that mpND (0.20 g, 8.5 mmol) was used instead of mND. The pure product was isolated as a white solid. Yield: 69% (0.15 g). ¹H NMR (400 MHz, CDCl₃): δ 8.62 (d, 1H, *J* = 4.88 Hz), 8.59 (d, 1H, *J* = 4.88 Hz), 8.15–8.12 (m, 6H), 7.53–7.40 (m, 14H), 7.33 (d, 1H, *J* = 5.04 Hz), 7.30 (d, 1H, *J* = 4.96 Hz), 2.93 (s, 3H), 2.92 (s, 3H), 2.86 (s, 3H). ¹³C NMR (100 MHz, CDCl₃): δ 165.42, 165.31, 165.13, 161.13, 160.78, 160.70, 153.50, 153.15, 153.11, 143.63, 143.59, 142.77, 142.62, 140.66, 140.39, 140.19, 139.91, 135.45, 134.82, 134.70, 129.64, 129.46, 129.32, 128.69, 128.67, 128.60, 127.69, 128.61, 125.38, 125.24, 124.87, 106.99, 106.61, 106.24, 17.73, 17.65. FAB-MS: calcd 774.19, *m/z* = 775.2 (M+H⁺). Anal. Found (Calcd) for C₄₅H₃₃GaN₆O₃: C, 69.80 (69.69); H, 4.27 (4.29); N, 10.72 (10.84).

Synthesis of Tris(4-hydroxy-8-methyl-1,5-naphthyridinato)indium (InmND₃). To a water solution (7.2 mL) were added mND (0.15 g, 0.94 mmol) and indium chloride (0.07 g, 0.32 mmol). The reaction mixture was stirred and heated at reflux temperature. An excess amount of potassium acetate was added to the solution to change the solution acidity from pH 3-4 to pH 7-8. During the reaction (ca. 1 h), the formation of a milky white solid was observed. However, the blue fluorescence from such a precipitate was barely discernible. After the removal of water by vacuum distillation, the resulting solid was subjected to Soxhlet extration by dichloromethane for 24 h. The extracted dichloromethane solution was evaporated until dryness, and the solid residue was further purified by zone-temperature sublimation. The pure product was isolated as an off-white solid. Yield: 76% (0.14 g). ¹H NMR (400 MHz, CDCl₃): δ 8.67 (d, 3H, J = 5.40 Hz), 8.33 (d, 3H, J = 4.80 Hz), 7.51 (dd, 3H, J = 4.79 Hz, J = 0.71 Hz), 6.95 (d, 3H, J = 5.41Hz), 2.83 (s, 9H). ¹³C NMR (100 MHz, CDCl₃): δ 165.73, 153.71, 153.68, 144.30, 144.22, 136.46, 125.04, 110.75, 18.23. FAB-MS: calcd 592.07, m/z = 593.0 (M+H⁺). Anal. Found (Calcd) for C₂₇H₂₁InN₆O₃: C, 54.79 (54.75); H, 3.46 (3.57); N, 14.07 (14.19).

Synthesis of Tris(4-hydroxy-2,8-dimethyl-1,5-naphthyridinato)indium (InmmND₃). This compound was synthesized in the same manner as InmND₃, except that mmND (0.17 g, 0.98 mmol) was used instead of mND. The pure product was isolated as an off-white solid. Yield: 81% (0.17 g). ¹H NMR (400 MHz, CDCl₃): δ 8.22 (d, 3H, J = 4.80 Hz), 7.43 (dd, 3H, J = 4.82 Hz, J = 0.68 Hz), 6.84 (s, 3H), 2.79 (s, 9H), 2.53 (s, 9H). ¹³C NMR (100 MHz, CDCl₃): δ 165.19, 163.02, 152.57, 143.74, 143.04, 135.36, 124.89, 110.57, 26.15, 18.04. FAB-MS: calcd 634.12, m/z = 635.1 (M+H⁺). Anal. Found (Calcd) for C₃₀H₂₇InN₆O₃: C, 56.49 (56.80); H, 4.24 (4.29); N, 12.96 (13.25).

Synthesis of Tris(4-hydroxy-8-dimethyl-2-phenyl-1,5-naphthyridinato)indium (InmpND₃). This compound was synthesized in the same manner as InmND₃, except that mpND (0.50 g, 2.1 mmol) was used instead of mND. However, the precipitate formed during the reaction was observed for blue fluorescence, and it was isolated by filtration. After washing with water, the solid was vacuum-dried and finally subjected to zone-temperature sublimation. The pure product was isolated as an off-white solid. Yield: 51% (0.30 g). ¹H NMR (400 MHz, CDCl₃): δ 8.34 (d, 3H, J = 4.80Hz), 8.15–8.12 (m, 6H), 7.53–7.51 (m, 6H), 7.49–7.40 (m, 9H), 2.91 (s, 9H). ¹³C NMR (100 MHz, CDCl₃): δ 165.99, 160.24, 153.78, 144.04, 143.62, 140.05, 135.77, 129.44, 128.63, 127.57, 125.15, 107.86, 17.99. MOLDI-TOF MS: calcd 820.17, m/z = 821.15 (M+H⁺). Anal. Found (Calcd) for $C_{45}H_{33}InN_6O_3$: C, 65.78 (65.86); H, 3.95 (4.05); N, 10.26 (10.24).

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Supporting Information Available: The synthesis and structural characterization data of chelating ligands, ND, mND, mmND, mpND, and their precursors are described. DSC thermograms of AlmpND₃, GampND₃, and InmpND₃ (Figure S1); EL characteristics (Figure S2) and data (Table S1) of nondoped GamND₃, GammND₃, InmND₃, or InmmND₃ OLEDs; absorption and photoluminescence spectra of AlmND₃ and rubrene as well as their solution fluorescence images (Figure S3) are given. The crystallographic information is listed in Table S2 and file (.cif) also given for AlND₃·CH₂Cl₂. This material is available free of charges via the Internet at http://pubs.acs.org.

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